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MTM23110

Silicon P-channel MOSFET

For switching circuits

■ Features

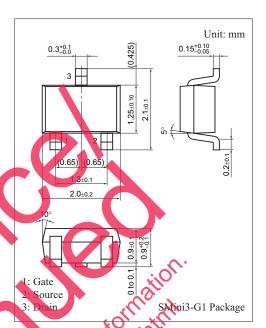
- Low voltage drive (1.8 V, 2.5 V, 4 V)
- Realization of low on-resistance, using extremely fine process

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Drain-source surrender voltage	V _{DSS}	-12	V	
Gate-source surrender voltage	V _{GSS}	±8	V	
Drain current	I_D	-4.0	A	
Peak drain current *1	I_{DP}	-16	A	
Power dissipation *2	P_{D}	500	mW	
Channel temperature	T _{ch}	150	°C	
Storage temperature	T _{stg}	-55 to ±150	°C	

Note) *1: Pulse width \leq 10 μ s, Duty Cycle \leq 1%

*2: Measuring on ceramic substrate at 40 mm × 38 mm × 0.1 mm Absolute maximum rating without heat sink for P_D is 150 mW



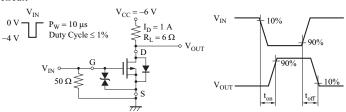
Marking Symbol. DM

■ Electrical Characteristics $T_a = 25$ C±3°

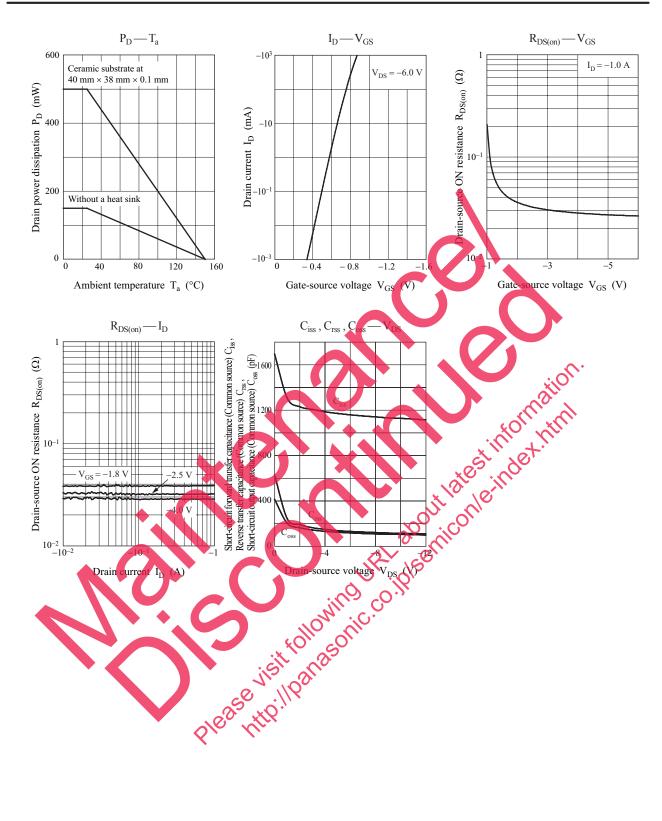
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Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source surrender voltage	$V_{ m DSS}$	$I_D = -1 \text{ mA}, V_{GS} = 0$	12			V
Drain-source cutoff current	I_{DSS}	$V_{\rm DS} = 12 V_{\rm N} V_{\rm GS} = 0$			-1.0	μΑ
Gate-source cutoff current	I_{GSS}	$V_{GS} = \pm 6.4 \text{ V}, V_{DS} = 0$			±10	μΑ
Gate threshold voltage	V _{TH}	$I_0 = -1.0 \text{ mA}, V_{DS} = 6.0 \text{ V}$	-0.3	- 0.65	-1.0	V
		$I_{\rm p} = -1 \text{A}, V_{\rm p} = -4.0 \text{V}$		30	40	
Drain-source ON resistance*1	R _{DS(on)}	$I_D = -0.5 \text{ A}, V_{GS} = -2.5 \text{ V}$		35	55	mΩ
		$I_D = 0.2 \text{ A}, V_{GS} = -1.8 \text{ V}$		50	75	
Forward transfer admittance *1	$ Y_{fs} $	$J_0 = -1.0 \text{ A, V}_{DS} = -10 \text{ V, f} = 1 \text{ kHz}$	3.5			S
Short-circuit forward transfer capacitance (Common source)	CSO	illogi		1200		pF
Short-circuit output capacitance (Common source)	e Coss	$V_{DS} = -10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		110		pF
Reverse transfer capacitance (Common source)	C _{rss}			110		pF
Turn-on time *2	t _{on}	$V_{DD} = -6 \text{ V}, V_{GS} = 0 \text{ V to } -4 \text{ V}, I_D = -1 \text{ A}$		50		ns
Turn-off time *2	t _{off}	$V_{DD} = -6 \text{ V}, V_{GS} = -4 \text{ V to } 0 \text{ V}, I_D = -1 \text{ A}$		300		ns

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

- 2. *1: Pulse measurement: Pulse width < 300 $\mu s,$ Duty Cycle < 2%
 - *2: t_{on} , t_{off} measurement circuit



MTM23110 Panasonic



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